DF005 THRU DF10

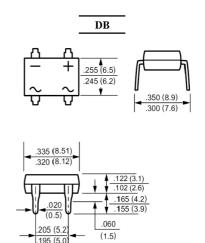
SINGLE-PHASE GLASS PASSIVATED SILICON BRIDGE RECTIFIER Reverse Voltage – 50 to 1000 Volts Forward Current – 1.0 Ampere

Features

- Glass passivated chip junction
- Low forward voltage drop
- High surge overload rating of 50 Amperes peak
- Ideal for printed circuit board
- High temperature soldering guaranteed: 260°C for 10 seconds

Mechanical Data

Case: Molded plastic, DB Epoxy: UL 94V-O rate flame retardant Terminals: Leads solderable per MIL-STD-202, method 208 guaranteed Mounting position: Any Weight: 0.02ounce, 0.4gram



Dimensions in inches and (millimeters)

Absolute Maximum Ratings and Characteristics

Ratings at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Image: Symbols DF00 DF01 DF02 DF04 DF06 DF08 DF10 Maximum Recurrent Peak Reverse Voltage V_{RRM} 50 100 200 400 600 800 1000 Maximum RMS Voltage V_{RMS} 35 70 140 280 420 560 700 Maximum DC Blocking Voltage V_{DC} 50 100 200 400 600 800 1000 Maximum Average Forward Rectified Current, add of C V_{DC} 500 100 200 400 600 800 1000 Maximum Average Forward Surge Current, 8.3ms site half-sine-wave superimposed on rated load (JEDEC retretretretretretretretretretretretretr										
$\begin{array}{c c c c c c c c c } \hline Maximum RMS Voltage & V_{RMS} & 35 & 70 & 140 & 280 & 420 & 560 & 700 \\ \hline Maximum DC Blocking Voltage & V_{DC} & 50 & 100 & 200 & 400 & 600 & 800 & 1000 \\ \hline Maximum Average Forward Rectified Current at T_A = 40 °C & 1 & & & & & & & & & & & & & & & & & $		Symbols	DF005	DF01	DF02	DF04	DF06	DF08	DF10	Units
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	aximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at $T_A = 40 ^{\circ}C$ I Peak Forward Surge Current, 8.3ms single half-sine-wave superimposed on rated load (JEDEC method) I Maximum Forward Voltage at 1A DC V _F Maximum Reverse Voltage at Rated DC Blocking Voltage at $T_A = 25^{\circ}C$ at $T_A = 125^{\circ}C$ I _R Typical Junction Capacitance ¹⁾ C _J 25 Typical Thermal Resistance ²⁾ R _{BJA} 40	aximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	V
at $T_A = 40 ^{\circ}$ CI1Peak Forward Surge Current, 8.3ms single half-sine-wave superimposed on rated load (JEDEC wethod)I50Maximum Forward Voltage at 1A DCVF1.1Maximum Reverse Voltage at Rated DC Blocking Voltageat $T_A = 25^{\circ}$ C at $T_A = 125^{\circ}$ CIR50Typical Junction Capacitance ¹⁾ CJ25Typical Thermal Resistance ²⁾ R40	aximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V
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at Rated DC Blocking Voltage at $T_A = 125^{\circ}C$ I_R 500 Typical Junction Capacitance ¹⁾ CJ 25 Typical Thermal Resistance ²⁾ R _{8JA} 40	aximum Forward Voltage at 1A DC	V _F				1.1				V
Typical Thermal Resistance ²⁾ R _{0JA} 40		— I _R								μA
	pical Junction Capacitance ¹⁾	CJ				25				pF
Turning Thermal Decision of 2	pical Thermal Resistance ²⁾	R _{0JA}				40				°C/W
	pical Thermal Resistance ²⁾	R _{eJL}				15				°C/W
Operating and storage temperature range T _J ,T _S -55 to +150	Operating and storage temperature range		-55 to +150						°C	

¹⁾ Measured at 1MHz and applied reverse voltage of 4VDC.

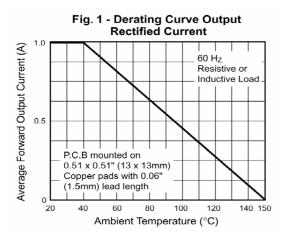
²⁾ Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.5 x 0.5" (13 x 13mm) copper pads.

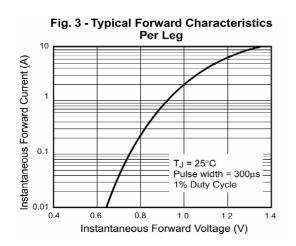


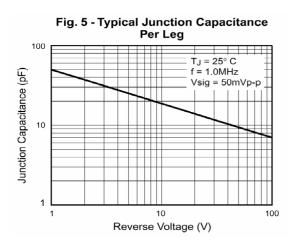




RATINGS AND CHARACTERISTIC CURVES







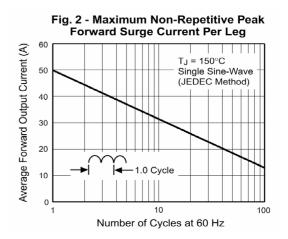


Fig. 4 - Typical Reverse Leakage Characteristics Per Leg

